Pressure

Freescale Semiconductor

10 kPa Uncompensated Silicon Pressure Sensors

The MPX10 series silicon piezoresistive pressure sensors provide a very accurate and linear voltage output, directly proportional to the applied pressure. These standard, low cost, uncompensated sensors permit manufacturers to design and add their own external temperature compensation and signal conditioning networks. Compensation techniques are simplified because of the predictability of Freescale's single element strain gauge design.

Features

- Low Cost
- Patented Silicon Shear Stress Strain Gauge Design •
- Ratiometric to Supply Voltage
- **Differential and Gauge Options**
- Durable Epoxy Unibody Element or Thermoplastic (PPS) Surface Mount Package

MPX10 Series

0 to 10 kPa (0 to 1.45 psi) 35 mV Full Scale Span (Typical)

Application Examples

- Air Movement Control
- **Environmental Control Systems**
- Level Indicators
- Leak Detection
- Medical Instrumentation
- **Industrial Controls**
- Pneumatic Control Systems
- Robotics

				ORDERI	NG INFORI	MATION			
Device Name	Package Case		# of Ports		Pressure Type			Device	
Device Maille	Options	No.	None	Single	Dual	Gauge	Differential	Absolute	Marking
Unibody Packa	ge (MPX10	Series)							
MPX10D	Tray	344	•				•		MPX10D
MPX10DP	Tray	344C			•		•		MPX10DP
MPX10GP	Tray	344B		•		•			MPX10GP
Small Outline F	ackage (MF	XV10G Se	eries)			•			
MPXV10GC6U	Rail	482A		•		•			MPXV10G
MPXV10GC7U	Rail	482C		•		•			MPXV10G

MPX10D CASE 344-15

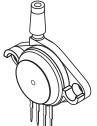
SMALL OUTLINE PACKAGE



MPXV10GC7U CASE 482C-03



UNIBODY PACKAGE



CASE 344B-01

MPX10GP





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MPXV10GC6U

CASE 482A-01

MPX10 Rev 14, 10/2008

Operating Characteristics

Table 1. Operating Characteristics ($V_S = 3.0 \text{ Vdc}$, $T_A = 25^{\circ}\text{C}$ unless otherwise noted, P1 > P2)

Characteristic	Symbol	Min	Тур	Мах	Units
Differential Pressure Range ⁽¹⁾	P _{OP}	0	—	10	kPa
Supply Voltage ⁽²⁾	V _S	_	3.0	6.0	V _{DC}
Supply Current	۱ _۵	_	6.0	—	mAdc
Full Scale Span ⁽³⁾	V _{FSS}	20	35	50	mV
Offset ⁽⁴⁾	V _{OFF}	0	20	35	mV
Sensitivity	$\Delta V / \Delta P$	_	3.5	—	mV/kPa
Linearity	_	-1.0	—	1.0	%V _{FSS}
Pressure Hysteresis (0 to 10 kPa)	_	_	±0.1	—	%V _{FSS}
Temperature Hysteresis	_	_	±0.5	—	%V _{FSS}
Temperature Coefficient of Full Scale Span	TCV _{FSS}	-0.22	—	-0.16	%V _{FSS} /°C
Temperature Coefficient of Offset	TCV _{OFF}	_	±15	—	μV/°C
Temperature Coefficient of Resistance	TCR	0.21	—	0.27	%Z _{IN} /°C
Input Impedance	Z _{IN}	400	—	550	Ω
Output Impedance	Z _{OUT}	750	—	1250	Ω
Response Time ⁽⁵⁾ (10% to 90%)	t _R	_	1.0	—	ms
Warm-Up Time ⁽⁶⁾	-	_	20	—	ms
Offset Stability ⁽⁷⁾	_		±0.5	—	%V _{FSS}

1. 1.0 kPa (kiloPascal) equals 0.145 psi.

2. Device is ratiometric within this specified excitation range. Operating the device above the specified excitation range may induce additional error due to device self-heating.

3. Full Scale Span (V_{FSS}) is defined as the algebraic difference between the output voltage at full rated pressure and the output voltage at the minimum rated pressure.

4. Offset (V_{OFF}) is defined as the output voltage at the minimum rated pressure.

5. Response Time is defined as the time for the incremental change in the output to go from 10% to 90% of its final value when subjected to a specified step change in pressure.

6. Warm-up Time is defined as the time required for the product to meet the specified output voltage after the pressure is stabilized.

7. Offset stability is the product's output deviation when subjected to 1000 hours of Pulsed Pressure, Temperature Cycling with Bias Test.

Maximum Ratings

Table 2. Maximum Ratings⁽¹⁾

Rating	Symbol	Value	Unit
Maximum Pressure (P1 > P2)	P _{MAX}	75	kPa
Burst Pressure (P1 > P2)	P _{BURST}	100	kPa
Storage Temperature	T _{STG}	-40 to +125	°C
Operating Temperature	T _A	-40 to +125	°C

1. Exposure beyond the specified limits may cause permanent damage or degradation to the device.

Figure 1 shows a schematic of the internal circuitry on the stand-alone pressure sensor chip.

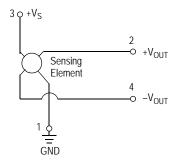


Figure 1. Uncompensated Pressure Sensor Schematic

Voltage Output versus Applied Differential Pressure

The output voltage of the differential or gauge sensor increases with increasing pressure applied to the pressure side (P1) relative to the vacuum side (P2). Similarly, output voltage increases as increasing vacuum is applied to the vacuum side (P2) relative to the pressure side (P1).

Temperature Compensation

Figure 2 shows the typical output characteristics of the MPX10 series over temperature.

Because this strain gauge is an integral part of the silicon diaphragm, there are no temperature effects due to differences in the thermal expansion of the strain gauge and the diaphragm, as are often encountered in bonded strain gauge pressure sensors. However, the properties of the strain gauge itself are temperature dependent, requiring that the device be temperature compensated if it is to be used over an extensive temperature range.

Temperature compensation and offset calibration can be achieved rather simply with additional resistive components, or by designing your system using the MPX2010D series sensor.

LINEARITY

Linearity refers to how well a transducer's output follows the equation: $V_{out} = V_{off}$ + sensitivity x P over the operating pressure range (Figure 3). There are two basic methods for calculating nonlinearity: 1) end point straight line fit or 2) a least squares best line fit. While a least squares fit gives the "best case" linearity error (lower numerical value), the calculations required are burdensome.

Conversely, an end point fit will give the "worst case" error (often more desirable in error budget calculations) and the calculations are more straightforward for the user. Freescale's specified pressure sensor linearities are based on the end point straight line method measured at the midrange pressure.

Figure 4 illustrates the differential or gauge configuration in the basic chip carrier (Case 344). A silicone gel isolates the die surface and wire bonds from the environment, while allowing the pressure signal to be transmitted to the silicon diaphragm.

The MPX10 series pressure sensor operating characteristics and internal reliability and qualification tests are based on use of dry air as the pressure media. Media other than dry air may have adverse effects on sensor performance and long term reliability. Contact the factory for information regarding media compatibility in your application.Refer to application note AN3728, for more information regarding media compatibility.

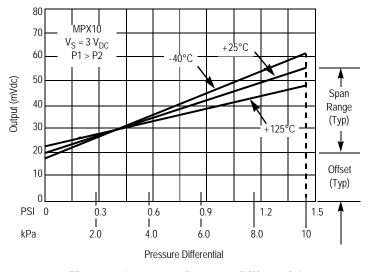


Figure 2. Output vs. Pressure Differential

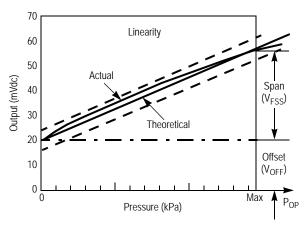
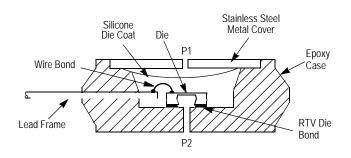
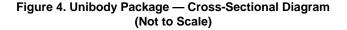


Figure 3. Linearity Specification Comparison





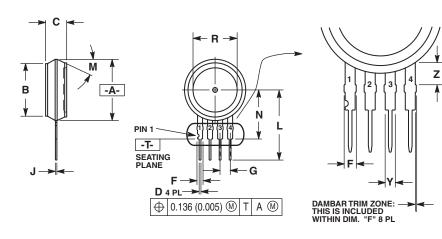
PRESSURE (P1)/VACUUM (P2) SIDE IDENTIFICATION TABLE

Freescale designates the two sides of the pressure sensor as the Pressure (P1) side and the Vacuum (P2) side. The Pressure (P1) side is the side containing silicone gel which isolates the die from the environment. The pressure sensor is designed to operate with positive differential pressure applied, P1 > P2.

The Pressure (P1) side may be identified by using the following table.

Part Number	Case Type	Pressure (P1) Side Identifier
MPX10D	344	Stainless Steel Cap
MPX10DP	344C	Side with Part Marking
MPX10GP	344B	Side with Port Attached
MPXV10GC6U	482A	Side with Port Attached
MPXV10GC7U	482C	Side with Port Attached

PACKAGE DIMENSIONS



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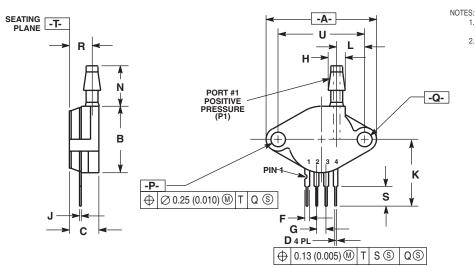
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1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 CONTROLLING DIMENSION: INCH.
 DIMENSION -A- IS INCLUSIVE OF THE MOLD STOP RING. MOLD STOP RING NOT TO EXCEED 16.00 (0.630).

	INC	HES	MILLIM	ETERS		
DIM	MIN	MAX	MIN	MAX		
Α	0.595	0.630	15.11	16.00		
В	0.514	0.534	13.06	13.56		
С	0.200	0.220	5.08	5.59		
D	0.016	0.020	0.41	0.51		
F	0.048	0.064	1.22	1.63		
G	0.100) BSC	2.54 BSC			
J	0.014	0.016	0.36	0.40		
L	0.695	0.725	17.65	18.42		
Μ	30°	NOM	30° I	NOM		
Ν	0.475	0.495	12.07	12.57		
R	0.430	0.450	10.92	11.43		
Y	0.048	0.052	1.22	1.32		
Ζ	0.106	0.118	2.68	3.00		

CASE 344-15 **ISSUE AA UNIBODY PACKAGE**

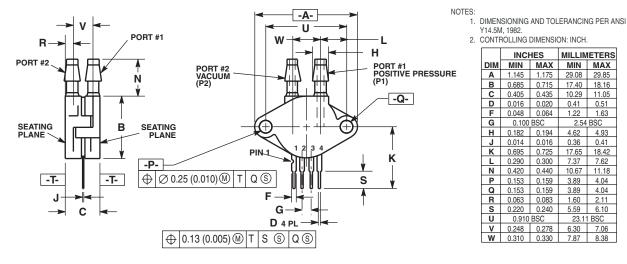


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	Y14.5M, 1982.								
2.	CONTROLLING DIMENSION: INCH.								
		INC	HES	MILLIM	ETERS				
	DIM		HES	MILLIM	ETERS MAX				

		1120		LILINO
DIM	MIN	MAX	MIN	MAX
Α	1.145	1.175	29.08	29.85
В	0.685	0.715	17.40	18.16
С	0.305	0.325	7.75	8.26
D	0.016	0.020	0.41	0.51
F	0.048	0.064	1.22	1.63
G	0.10	0 BSC	2.54	BSC
Н	0.182	0.194	4.62	4.93
J	0.014	0.016	0.36	0.41
Κ	0.695	0.725	17.65	18.42
L	0.290	0.300	7.37	7.62
Ν	0.420	0.440	10.67	11.18
Р	0.153	0.159	3.89	4.04
Q	0.153	0.159	3.89	4.04
R	0.230	0.250	5.84	6.35
s	0.220	0.240	5.59	6.10
U	0.91	0 BSC	23.11	BSC

CASE 344B-01 **ISSUE B UNIBODY PACKAGE**

PACKAGE DIMENSIONS



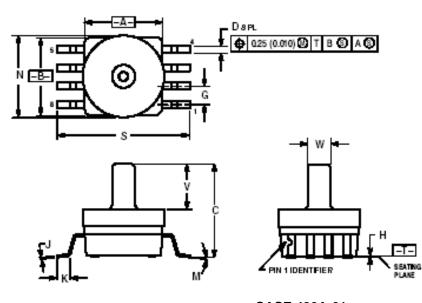
2. CONTROLLING DIMENSION: INCH. INCHES MILLIMETERS DIM MIN MAX MIN MAX А 1.145 1.175 29.08 29.85 **B** 0.685 0.715 17.40 18.16 C 0.405 0.435 10.29 11.05 0.016 0.020 0.048 0.064 D 0.41 0.51 1.22 1.63 F G 0.100 BSC 2.54 BSC 0.182 0.194 4.62 4.93 H J 0.014 0.016 0.36 0.41
 K
 0.695
 0.725

 L
 0.290
 0.300
 17.65 18.42 7.37 7.62 N 0.420 0.440 10.67 11.18 Ρ 0.153 0.159 3.89 4.04 Q 0.153 0.159 R 0.063 0.083 3.89 4.04 1.60 2.11 S 0.220 0.240 5.59 6.10 U
 U
 0.910 BSC
 23.11 BSC

 V
 0.248
 0.278
 6.30
 7.06
 W 0.310 0.330 7.87 8.38

Y14.5M, 1982.

CASE 344C-01 **ISSUE B UNIBODY PACKAGE**



CASE 482A-01 **ISSUE A** SMALL OUTLINE PACKAGE

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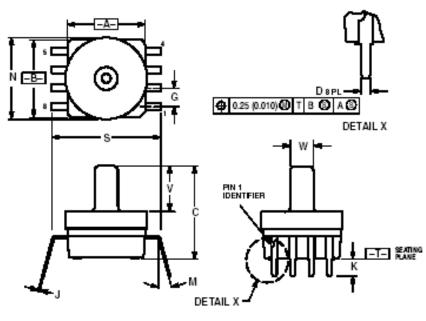
PROTRUSION. MAXIMUM NOLD PROTRUSION 0.15 (0.006). ALL VERTICAL SURRICES 5° TYPICAL DRAFT.

5

	NC	HES	NULLINETERS	
DIN	NIN	MAX	2	NAX
A	0.415	0.425	10.54	10.79
В	0.415	0.425	10.54	10.79
C	0.500	0.520	12.70	1321
0	0.038	0.042	0.96	1.07
6	0.100	BSC	254 BSC	
н	0.002	0.010	0.05	0.25
J.	0.009	0.011	0.23	0.28
ĸ	0.061	0.071	1.55	1.80
	Û₽.	7 -	0 -	7 0
N	0.444	0.448	11.28	11.38
8	0.709	0.725	18.01	18.41
V.	0.245	0.255	6.22	6.48
W	0.115	0.125	2.92	317

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NOTES: 1. CIMENIS ONING AND TO LEPANCING PER ANSI Y145M, 1982 2. CONTROLLING DIMENIS ON: INCH. 3. CIMENIS ON A AND B DONOT INCLUDE NO ID PROTRUSION 4. MAXIMUM INDLD PROTRUSION 0.15 (0.008) 5. ALL VERTICAL SURFACES 5° TYPICAL DRAFT. 8. CIMENIS ON S TO CENTER OF LEAD WHEN PORMED RARALEL.

	- NC	HES	NULLINETERS	
DIN	NN	MAX	NN	NAX
A	0.415	0.425	1054	10.79
8	0.415	0.425	1054	10.79
ĉ	0.500	0.520	12.70	1321
D	0.026	0.034	0.66	0.864
6	0.100	BSC	2.54 B8C	
1	0.009	0.011	0.23	0.28
K	0.100	0.120	254	305
N.	0 -	15 ¤	0 0	_ 15 ¤
N	0.444	0.448	11.28	11.38
8	0.540	0.580	13.72	1422
V	0.245	0.255	6.22	6.48
W	0.115	0.125	2.92	817

CASE 482C-03 **ISSUE B** SMALL OUTLINE PACKAGE

MPX10

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